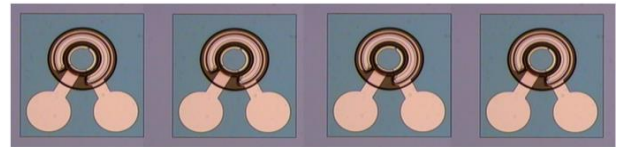


Features

- : Two top-side wire bond pads
- : AR coated for 850nm
- : Data rate up to 25Gbps
- : Low dark current and low capacitance
- : 1x4 Chips

Description



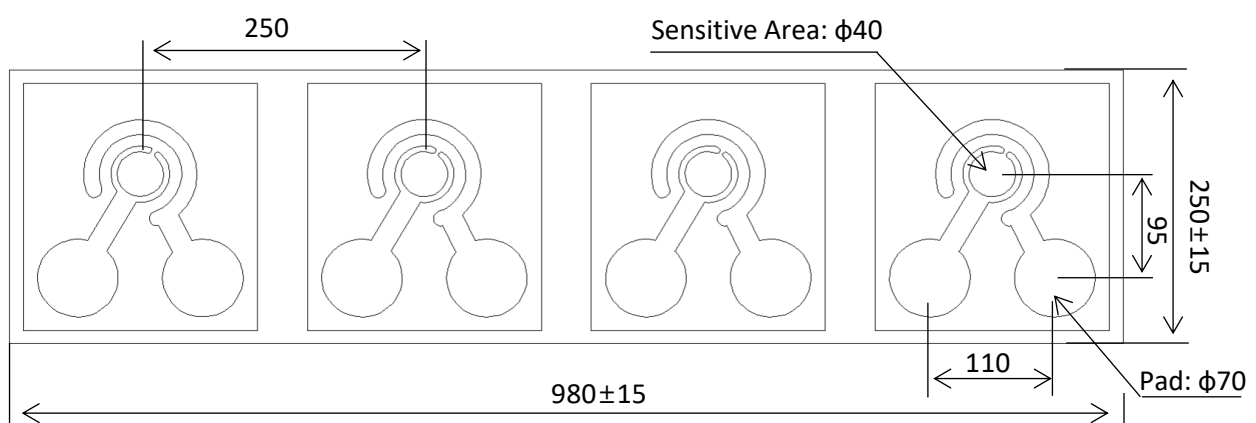
Applications

- : High speed Data Communications
- : Fiber Channel
- : Gigabit Ethernet
- : Parallel Optical Interconnects

Absolute Maximum Ratings

Parameter	Rating
Storage Temperature	-40 to 100 °C
Operating Temperature	-40 to 85 °C
Forward Current	10mA
Reverse Voltage	40V

Dimensions



unit : μm

Die Height : $150 \pm 15 \mu\text{m}$

**Electro-Optics Characteristics ($T_a=25^{\circ}\text{C}$ unless otherwise stated)**

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Sensitive Area	D		40		μm	In diameter
Responsivity	R		0.6		A/W	$V_R = 1.6\text{ V}$, $\lambda = 850\text{ nm}$
Dark Current	I_D			1.0	nA	$V_R = 2\text{ V}$
Breakdown Voltage	V_B	20			V	$I_r = 1\mu\text{A}$
Capacitance	C	0.08		0.20	pF	$V_R = 3\text{ V}$, $f = 1\text{ MHz}$
Modulation bandwidth	f_{dB}	16	20		GHz	50 Ω load, $V_R = 3\text{ V}$
Peak Wavelength	λ		850		nm	

Notes

- * Substrate : Semi-insulating GaAs
- * These specifications are subject to change without notice

NOTICE

The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product